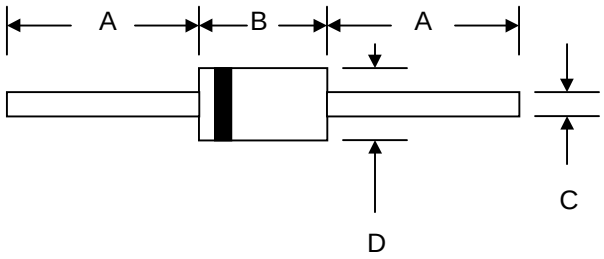
1N5400 – 1N5408

3.0A SILICON RECTIFIER

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability



DO-201AD		
Dim	**Min**	**Max**
A	24.5	—
B	7.20	9.50
C	1.10	1.30
D	5.00	5.60
All Dimensions in mm		

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Epoxy: UL 94V-O rate flame retardant
- **Lead Free: For RoHS / Lead Free Version,**

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	1N 5400	1N 5401	1N 5402	1N 5404	1N 5406	1N 5407	1N 5408	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T_A = 75°C	I_O	3.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	200							A
Forward Voltage @I_F = 3.0A	V_{FM}	1.0							V
Peak Reverse Current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I_{RM}	5.0 100							μA
Typical Junction Capacitance (Note 2)	C_j	50							pF
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	18							K/W
Operating Temperature Range	T_j	-55 to +150							°C
Storage Temperature Range	T_{STG}	-55 to +150							°C

***Glass passivated forms are available upon request**

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case
2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

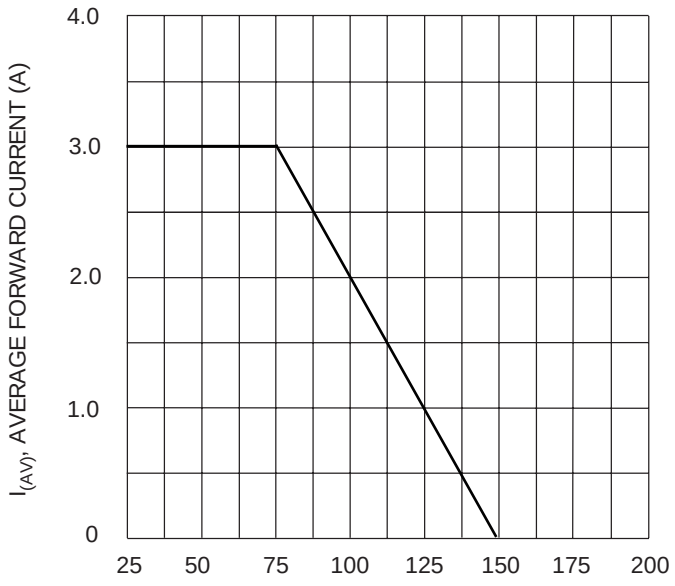


Fig. 1 Forward Current Derating Curve

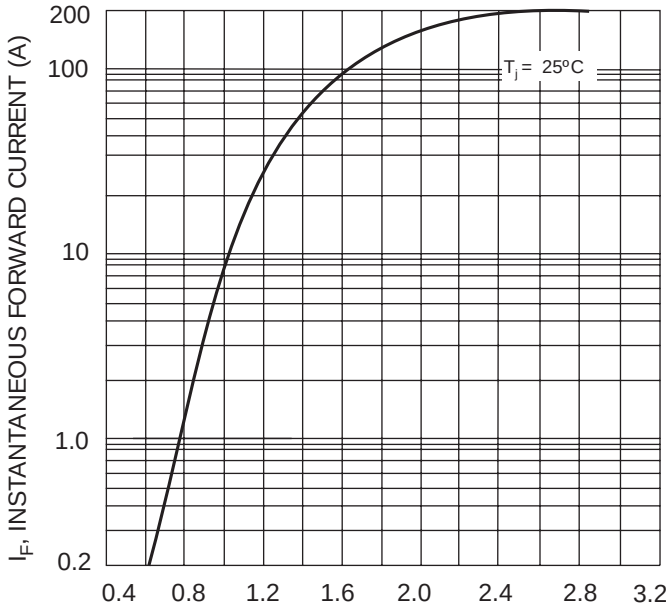


Fig. 2 Typical Forward Characteristics

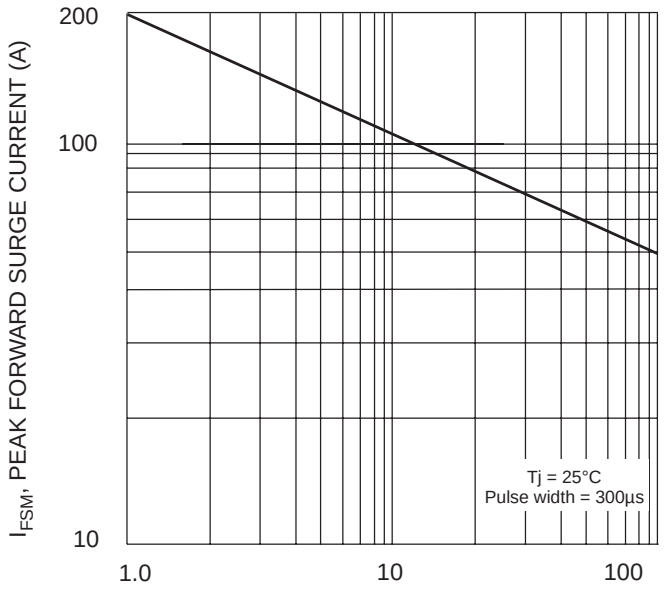


Fig. 3 Maximum Non-Repetitive Surge Current

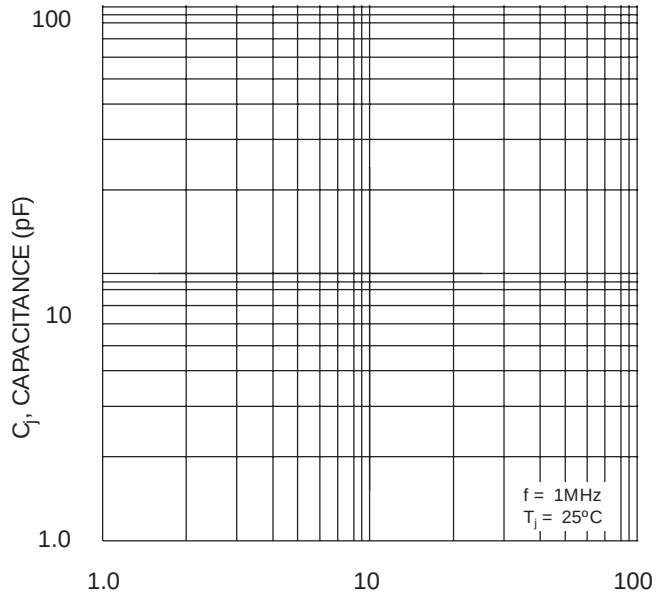


Fig. 4 Typical Junction Capacitance